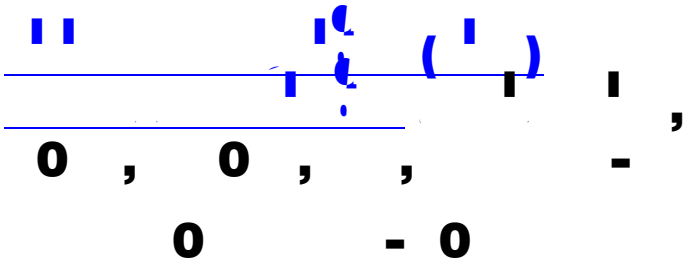

Description

Features

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Applications

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MOSFET MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Parameter		Ratings	Unit
V_{RRM}	Peak Repetitive Reverse Voltage		650	V
E_{AS}	Single Pulse Avalanche Energy (Note 1)		49	mJ
I_F	Continuous Rectified Forward Current	@ T_C < 25°C	23.6	A
		@ T_C < 140°C	10	
$I_{F, Max}$	Non−Repetitive Peak Forward Surge Current	T_C = 25°C, 10 μs	600	A
		T_C = 150°C, 10 μs	554	
$I_{F, SM}$	Non−Repetitive Forward Surge Current, T_C = 25°C	Half−Sine Pulse, t_p = 8.3 ms	45	A
P_{tot}	Power Dissipation	T_C = 25°C	75	W
		T_C = 150°C	12.5	
T_J, T_{STG}	Operating and Storage Temperature Range		−55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E_{AS} of 49 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 14 A, V = 50 V.

SCALE 1:1

D^2PAK-3 (TO−263, 3−LEAD)
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ISSUE F

DATE 11 MAR 2021